I claim:

1. An integrated memory, comprising:

bit lines;

word lines intersecting said bit lines at points of intersection;

memory cells disposed at said points of intersection between said word lines and said bit lines;

at least one reference word line intersecting said bit lines at points of intersection;

reference cells disposed at said points of intersection between said at least one reference word line and said bit lines, said reference cells generate a reference potential on said bit lines before an access operation to one of said memory cells;

a redundant word line intersecting said bits lines at points of intersection;

redundant memory cells disposed at said points of intersection between said redundant word line and said bit lines; and

a programmable activation unit having a programming state governing if said redundant word line connected to said redundant memory cells replaces one of said word lines connected to said memory cells or said at least one reference word line connected to said reference cells during operation of the integrated memory.

2. The integrated memory according to claim 1, wherein:

said programmable activation unit has a first subunit and a second subunit connected to said first subunit, said first subunit is used to distinguish if said redundant word line replaces one of said word lines or said reference word line during the operation of the integrated memory, said second subunit determines an instant at which said redundant word line is activated by said programmable activation unit during the access operation to one of said memory cells;

if said reference word line is being replaced by said redundant word line, said second subunit activates said redundant word line for generating the reference potential, before one of said word lines is activated; and

if one of said word lines is being replaced by said redundant word line, said second subunit does not activate said

redundant word line until after said reference word line has been activated for generating the reference potential.